Vincotech

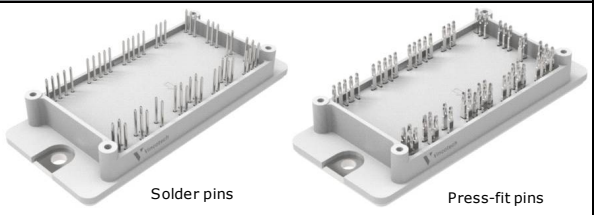
30-F212PMA100M7-L880A79
30-P212PMA100M7-L880A79Y
datasheet

***flow* PIM 2** **1200 V / 100 A**

Features

- IGBT M7 with low V_{CEsat} and improved EMC behavior
- Open emitter configuration
- Compact and low inductive design
- Built-in NTC

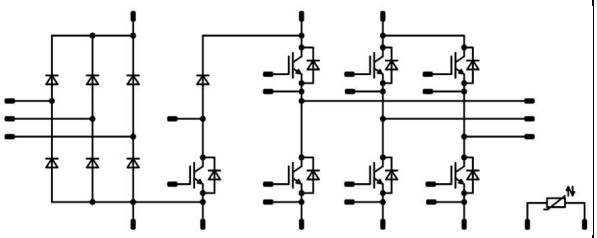
flow 2 17 mm housing



Target applications

- Industrial Drives

Schematic



Types

- 30-F212PMA100M7-L880A79
- 30-P212PMA100M7-L880A79Y

Maximum Ratings

T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Condition	Value	Unit
Rectifier				
Peak Repetitive Reverse Voltage	V_{RRM}		1600	V
Continuous (direct) forward current	I_F		75	A
Surge (non-repetitive) forward current	I_{FSM}	t_p = 10 ms, sin 180° T_j = 150 °C	890	A
Surge current capability	I^2t		3960	A^2s
Total power dissipation	P_{tot}	$T_j = T_{jmax}$ T_s = 80 °C	156	W
Maximum Junction Temperature	T_{jmax}		150	°C

Maximum Ratings

T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Condition	Value	Unit
Inverter Switch				
Collector-emitter voltage	V_{CES}		1200	V
Collector current	I_C		100	A
Repetitive peak collector current	I_{CRM}	t_p limited by T_{jmax}	200	A
Total power dissipation	P_{tot}	T_j = T_{jmax} T_s = 80 °C	222	W
Gate-emitter voltage	V_{GES}		±20	V
Maximum junction temperature	T_{jmax}		175	°C
Inverter Diode				
Peak repetitive reverse voltage	V_{RRM}		1200	V
Continuous (direct) forward current	I_F	T_j = T_{jmax} T_s = 80 °C	81	A
Repetitive peak forward current	I_{FRM}		200	A
Total power dissipation	P_{tot}	T_j = T_{jmax} T_s = 80 °C	165	W
Maximum junction temperature	T_{jmax}		175	°C
Brake Switch				
Collector-emitter voltage	V_{CES}		1200	V
Collector current	I_C		75	A
Repetitive peak collector current	I_{CRM}	t_p limited by T_{jmax}	150	A
Total power dissipation	P_{tot}	T_j = T_{jmax} T_s = 80 °C	190	W
Gate-emitter voltage	V_{GES}		±20	V
Maximum junction temperature	T_{jmax}		175	°C
Brake Diode				
Peak repetitive reverse voltage	V_{RRM}		1200	V
Continuous (direct) forward current	I_F		35	A
Repetitive peak forward current	I_{FRM}		70	A
Total power dissipation	P_{tot}	T_j = T_{jmax} T_s = 80 °C	77	W
Maximum junction temperature	T_{jmax}		175	°C

Maximum Ratings

T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Condition	Value	Unit
Brake Sw. Protection Diode				
Peak repetitive reverse voltage	V_{RRM}		1200	V
Continuous (direct) forward current	I_F		5	A
Repetitive peak forward current	I_{FRM}		10	A
Total power dissipation	P_{tot}	T_j = T_{jmax} T_s = 80 °C	27	W
Maximum junction temperature	T_{jmax}		175	°C
Module Properties				
Thermal Properties				
Storage temperature	T_{stg}		-40…+125	°C
Operation temperature under switching condition	T_{jop}		-40…(T_{jmax} - 25)	°C
Isolation Properties				
Isolation voltage	V_{isol}	DC Test Voltage* t_p = 2 s	4000	V
		AC Voltage t_p = 1 min	2500	V
Creepage distance			min. 12,7	mm
Clearance			12,03	mm
Comparative Tracking Index	CTI		> 200	

*100 % tested in production

Characteristic Values

Parameter	Symbol	Conditions					Value			Unit
			V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	
Rectifier										
Static										
Forward voltage	V_F				75	25 125 150		1,10 1,04 1,05	1,8	V
Reverse leakage current	I_r			1600		25 145				µA
Thermal										
Thermal resistance junction to sink	$R_{th(j-s)}$	λ_{paste} = 3,4 W/mK (PSX)						0,45		K/W

Characteristic Values

Parameter	Symbol	Conditions					Value			Unit
			V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	
Inverter Switch										
Static										
Gate-emitter threshold voltage	$V_{GE(th)}$	$V_{GE} = V_{CE}$			0,01	25	5,4	6	6,6	V
Collector-emitter saturation voltage	V_{CEsat}		15		100	25 125 150		1,53 1,70 1,75	2,05	V
Collector-emitter cut-off current	I_{CES}		0	1200		25			110	µA
Gate-emitter leakage current	I_{GES}		20	0		25			500	nA
Internal gate resistance	r_g							none		Ω
Input capacitance	C_{ies}		0	10		25		21000		pF
Output capacitance	C_{oes}							700		
Reverse transfer capacitance	C_{res}							280		
Gate charge	Q_g		15	600	100	25		650		nC
Thermal										
Thermal resistance junction to sink	$R_{th(j-s)}$	λ_{paste} = 3,4 W/mK (PSX)						0,43		K/W
Dynamic										
Turn-on delay time	$t_{d(on)}$	R_{goff} = 2 Ω R_{gon} = 2 Ω	±15	600	100	25 125 150		118 118 118		ns
Rise time	t_r					25 125 150		10 12 13		
Turn-off delay time	$t_{d(off)}$					25 125 150		174 200 206		
Fall time	t_f					25 125 150		83 96 107		
Turn-on energy (per pulse)	E_{on}	Q_{rFWD} = 11,6 µC Q_{rFWD} = 17,3 µC Q_{rFWD} = 19,2 µC				25 125 150		3,26 4,87 5,37		mWs
Turn-off energy (per pulse)	E_{off}					25 125 150		6,61 8,77 9,49		

Characteristic Values

Parameter	Symbol	Conditions					Value			Unit
			V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	
Inverter Diode										
Static										
Forward voltage	V_F				100	25 125 150		1,82 1,96 1,97	2,1	V
Reverse leakage current	I_R			1200		25			60	µA
Thermal										
Thermal resistance junction to sink	$R_{th(j-s)}$	λ_{paste} = 3,4 W/mK (PSX)						0,58		K/W
Dynamic										
Peak recovery current	I_{RRM}	di/dt = 9387 A/µs di/dt = 7872 A/µs di/dt = 8350 A/µs	±15	600	100	25 125 150		178 166 165		A
Reverse recovery time	t_{rr}					25 125 150		149 312 339		ns
Recovered charge	Q_r					25 125 150		11,60 17,27 19,18		µC
Reverse recovered energy	E_{rec}					25 125 150		5,14 7,75 8,59		mWs
Peak rate of fall of recovery current	$(di_{rf}/dt)_{max}$					25 125 150		4044 2649 2147		A/µs

Characteristic Values

Parameter	Symbol	Conditions					Value			Unit
			V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	
Brake Switch										
Static										
Gate-emitter threshold voltage	$V_{GE(th)}$	$V_{GE} = V_{CE}$			0,0075	25	5,4	6	6,6	V
Collector-emitter saturation voltage	V_{CEsat}		15		75	25 125 150		1,55 1,70 1,75	2,05	V
Collector-emitter cut-off current	I_{CES}		0	1200		25			110	µA
Gate-emitter leakage current	I_{GES}		20	0		25			500	nA
Internal gate resistance	r_g							4		Ω
Input capacitance	C_{ies}		0	10		25		16000		pF
Output capacitance	C_{oes}							480		
Reverse transfer capacitance	C_{res}							190		
Gate charge	Q_g		15	600	75	25		490		nC
Thermal										
Thermal resistance junction to sink	$R_{th(j-s)}$	λ_{paste} = 3,4 W/mK (PSX)						0,50		K/W
Dynamic										
Turn-on delay time	$t_{d(on)}$	R_{goff} = 16 Ω R_{gon} = 16 Ω	15/0	700	75	25 125 150		242 232 227		ns
Rise time	t_r					25 125 150		99 113 119		
Turn-off delay time	$t_{d(off)}$					25 125 150		847 919 938		
Fall time	t_f					25 125 150		41 54 56		
Turn-on energy (per pulse)	E_{on}	Q_{rFWD} = 5,3 µC Q_{rFWD} = 7,7 µC Q_{rFWD} = 8,9 µC				25 125 150		12,18 14,53 15,39		mWs
Turn-off energy (per pulse)	E_{off}					25 125 150		7,01 9,35 9,97		

Characteristic Values

Parameter	Symbol	Conditions					Value			Unit
			V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	
Brake Diode										
Static										
Forward voltage	V_F				35	25 125 150		1,66 1,76 1,75	2,1	V
Reverse leakage current	I_R			1200		25			40	µA
Thermal										
Thermal resistance junction to sink	$R_{th(j-s)}$	λ_{paste} = 3,4 W/mK (PSX)						1,24		K/W
Dynamic										
Peak recovery current	I_{RRM}	di/dt = 723 A/µs di/dt = 738 A/µs di/dt = 572 A/µs	15/0	700	75	25 125 150		26 26 27		A
Reverse recovery time	t_{rr}					25 125 150		411 540 599		ns
Recovered charge	Q_r					25 125 150		5,29 7,70 8,85		µC
Reverse recovered energy	E_{rec}					25 125 150		1,96 3,11 3,67		mWs
Peak rate of fall of recovery current	$(di_{rf}/dt)_{max}$					25 125 150		48 51 47		A/µs
Brake Sw. Protection Diode										
Static										
Forward voltage	V_F				5	25 125 150		1,57 1,65 1,65	2,1	V
Reverse leakage current	I_R			1200		25			20	µA
Thermal										
Thermal resistance junction to sink	$R_{th(j-s)}$	λ_{paste} = 3,4 W/mK (PSX)						3,50		K/W

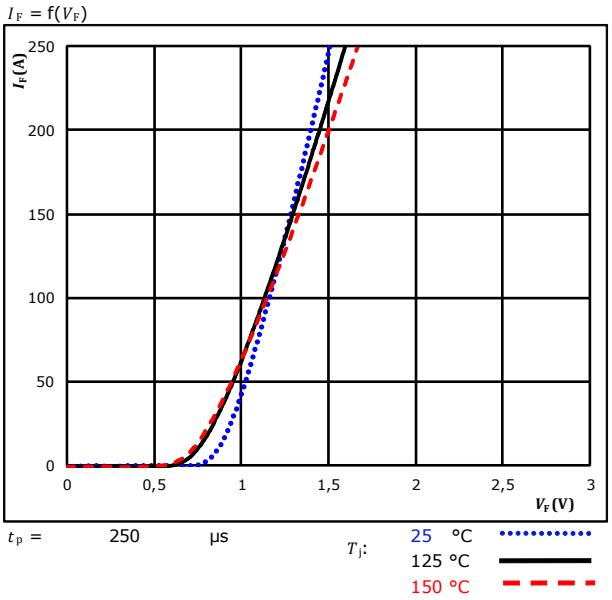
Characteristic Values

Parameter	Symbol	Conditions					Value			Unit
			V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	
Thermistor										
Rated resistance	R					25		22		kΩ
Deviation of R_{100}	$\Delta_{R/R}$	R_{100} = 1484 Ω				100	-5		5	%
Power dissipation	P					25		5		mW
Power dissipation constant						25		1,5		mW/K
B-value	$B_{(25/50)}$	Tol. ±1 %				25		3962		K
B-value	$B_{(25/100)}$	Tol. ±1 %				25		4000		K
Vincotech NTC Reference									I	

Rectifier Characteristics

figure 1. **Rectifier Diode**

Typical forward characteristics

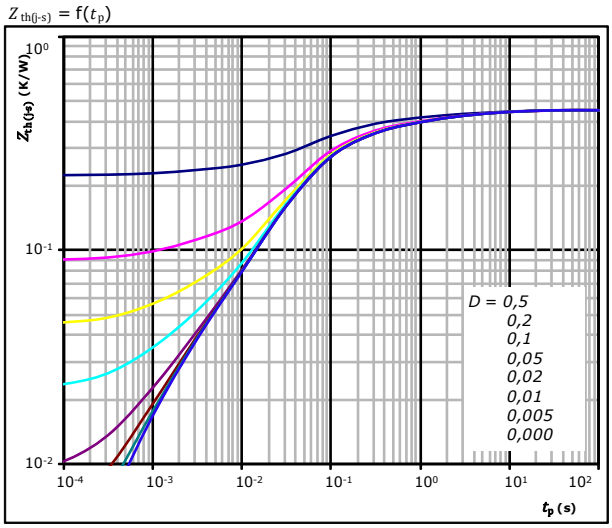


t_p = 250 µs

T_j: 25 °C
125 °C
150 °C

figure 2. **Rectifier Diode**

Transient thermal impedance as a function of pulse width



D = t_p / T

$R_{th(j-s)}$ = 0,45 K/W

Diode thermal model values

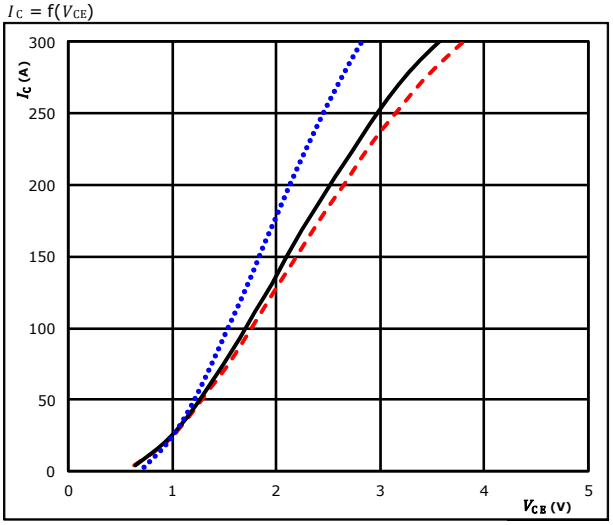
R (K/W)	τ (s)
3,06E-02	7,38E+00
5,87E-02	1,30E+00
1,21E-01	1,90E-01
2,00E-01	4,49E-02
2,12E-02	9,83E-03
1,85E-02	1,38E-03

Inverter Switch Characteristics

figure 1. **IGBT**

Typical output characteristics

$I_C = f(V_{CE})$

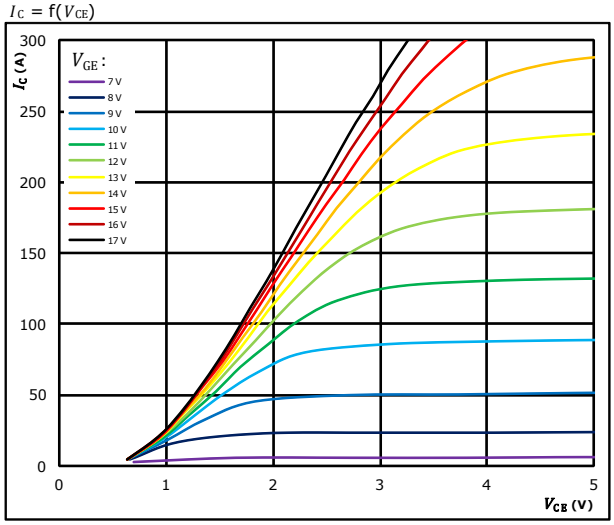


t_p =	250	µs		25 °C
V_{GE} =	15	V	T_j:	125 °C
				150 °C

figure 2. **IGBT**

Typical output characteristics

$I_C = f(V_{CE})$

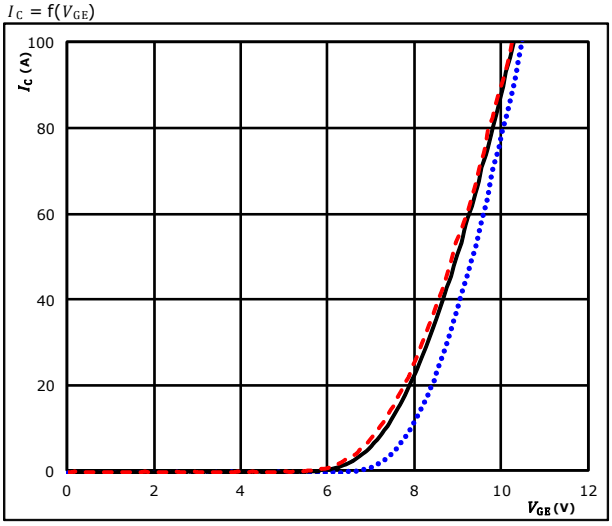


t_p =	250	µs
T_j =	150	°C
V_{GE} from	7 V to 17 V in steps of 1 V	

figure 3. **IGBT**

Typical transfer characteristics

$I_C = f(V_{GE})$

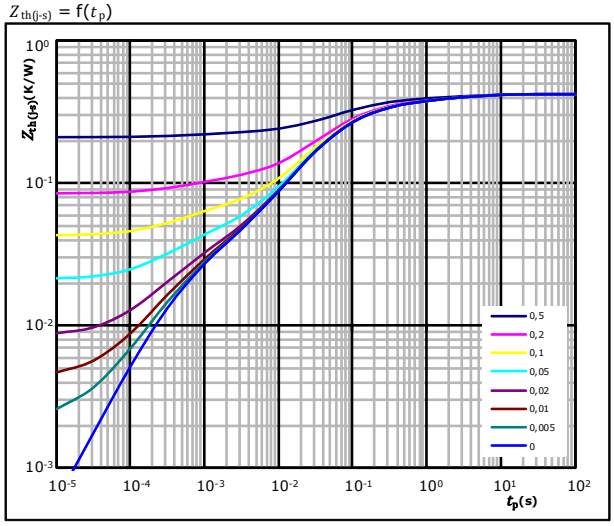


t_p =	100	µs		25 °C
V_{CE} =	10	V	T_j:	125 °C
				150 °C

figure 4. **IGBT**

Transient thermal impedance as function of pulse duration

$Z_{th(j-s)} = f(t_p)$



D =	t_p / T	
$R_{th(j-s)}$ =	0,43	K/W

IGBT thermal model values

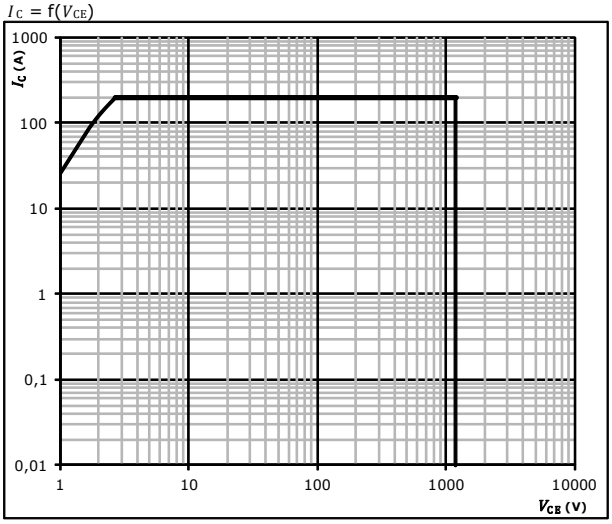
R (K/W)	τ (s)
3,38E-02	4,81E+00
4,26E-02	1,02E+00
7,30E-02	2,26E-01
1,67E-01	6,44E-02
8,34E-02	1,89E-02
1,52E-02	1,20E-03
1,24E-02	3,17E-04

Inverter Switch Characteristics

figure 5. **IGBT**

Safe operating area

$I_C = f(V_{CE})$



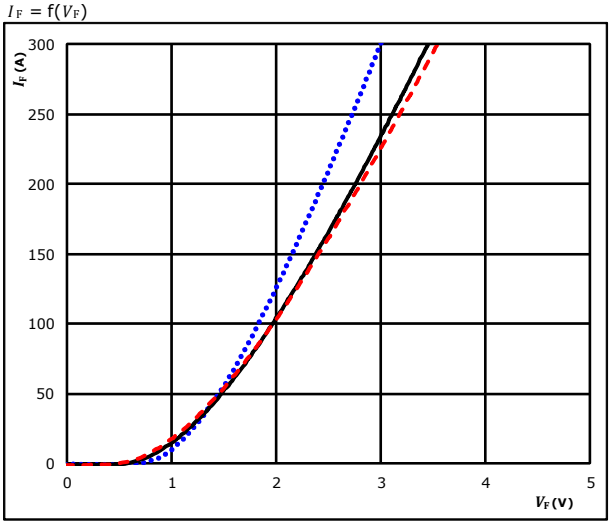
D =	single pulse	
T_s =	80	ºC
V_{GE} =	±15	V
T_j =	T_{jmax}	

Inverter Diode Characteristics

figure 1. **FWD**

Typical forward characteristics

$I_F = f(V_F)$



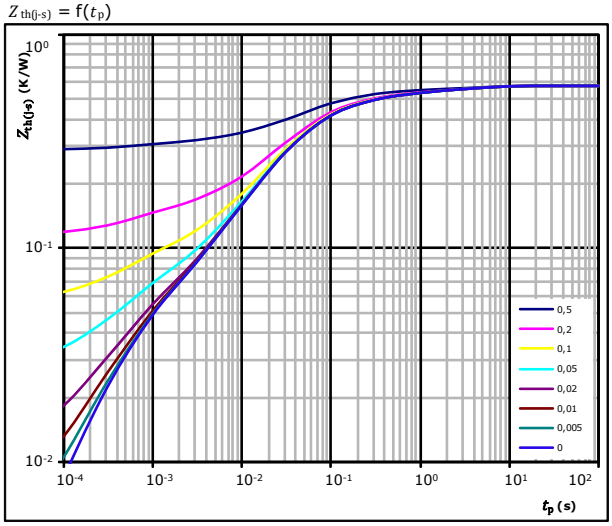
t_p = 250 µs

T_j: 25 °C
125 °C
150 °C

figure 2. **FWD**

Transient thermal impedance as a function of pulse width

$Z_{th(j-s)} = f(t_p)$



D = t_p / T

$R_{th(j-s)}$ = 0,58 K/W

FWD thermal model values

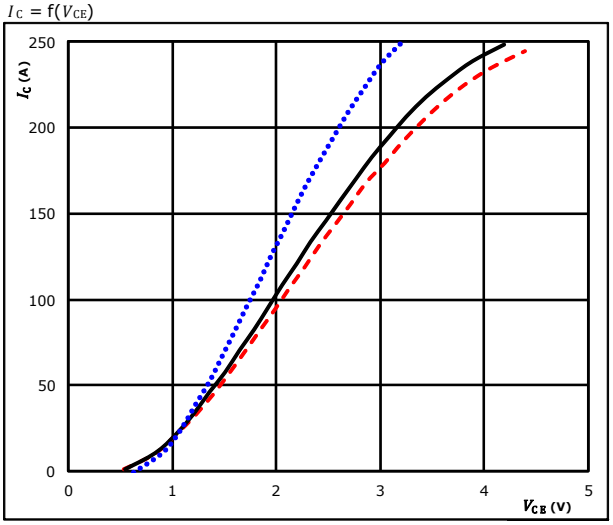
R (K/W)	τ (s)
4,89E-02	3,41E+00
7,07E-02	4,06E-01
2,02E-01	7,46E-02
1,90E-01	2,27E-02
3,24E-02	3,47E-03
3,35E-02	4,78E-04

Brake Switch Characteristics

figure 1. **IGBT**

Typical output characteristics

$I_C = f(V_{CE})$

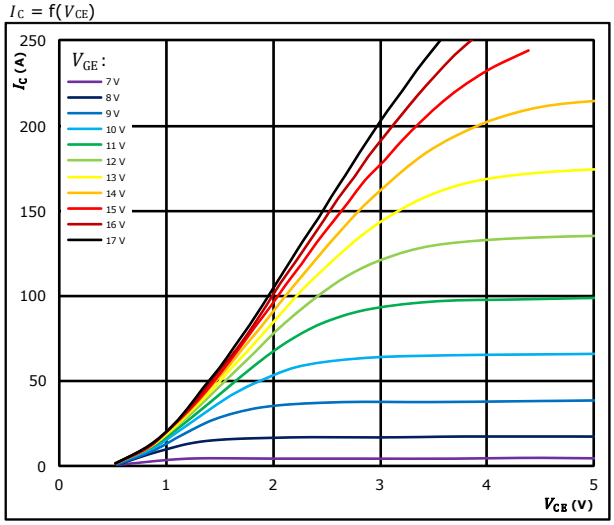


t_p =	250	µs		25 °C	
V_{GE} =	15	V	T_j:	125 °C	
				150 °C	

figure 2. **IGBT**

Typical output characteristics

$I_C = f(V_{CE})$

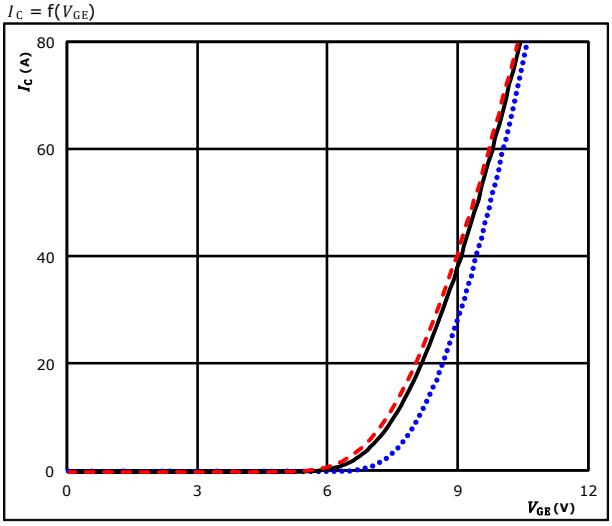


t_p =	250	µs	
T_j =	150	°C	
V_{GE} from	7 V to 17 V in steps of 1 V		

figure 3. **IGBT**

Typical transfer characteristics

$I_C = f(V_{GE})$

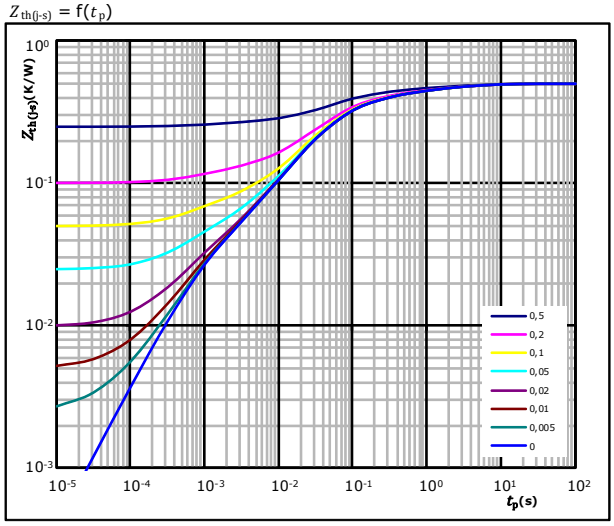


t_p =	100	µs		25 °C	
V_{CE} =	10	V	T_j:	125 °C	
				150 °C	

figure 4. **IGBT**

Transient thermal impedance as function of pulse duration

$Z_{th(j-s)} = f(t_p)$



D =	t_p / T	
$R_{th(j-s)}$ =	0,50	K/W

IGBT thermal model values

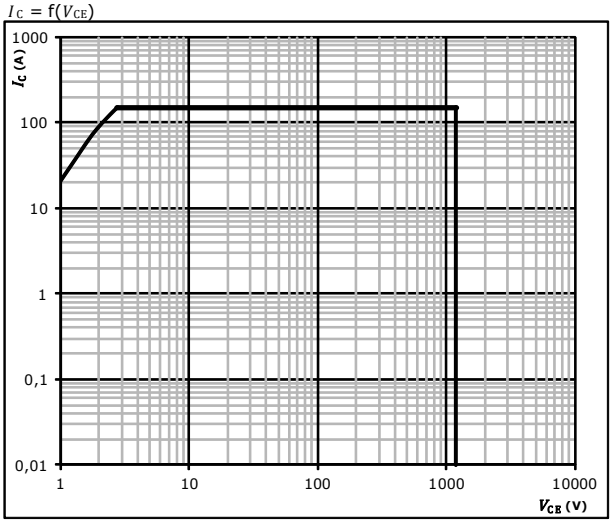
R (K/W)	τ (s)
3,92E-02	4,73E+00
6,01E-02	9,48E-01
1,18E-01	1,70E-01
2,25E-01	3,80E-02
3,32E-02	9,18E-03
2,48E-02	8,63E-04

Brake Switch Characteristics

figure 5. **IGBT**

Safe operating area

$I_C = f(V_{CE})$



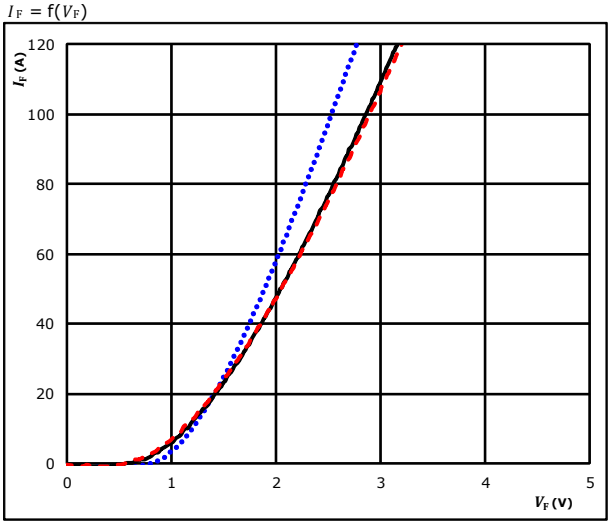
D =	single pulse	
T_s =	80	ºC
V_{GE} =	±15	V
T_j =	T_{jmax}	

Brake Diode Characteristics

figure 1. **FWD**

Typical forward characteristics

$I_F = f(V_F)$



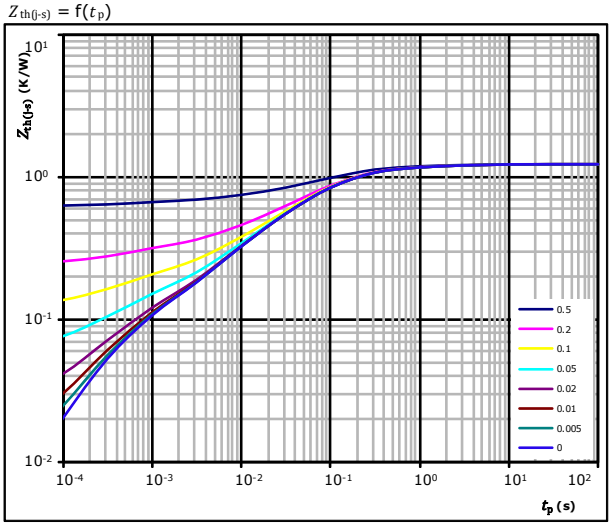
t_p = 250 µs

T_j: 25 °C
125 °C
150 °C

figure 2. **FWD**

Transient thermal impedance as a function of pulse width

$Z_{th(j-s)} = f(t_p)$



D = t_p / T

$R_{th(j-s)}$ = 1,24 K/W

FWD thermal model values

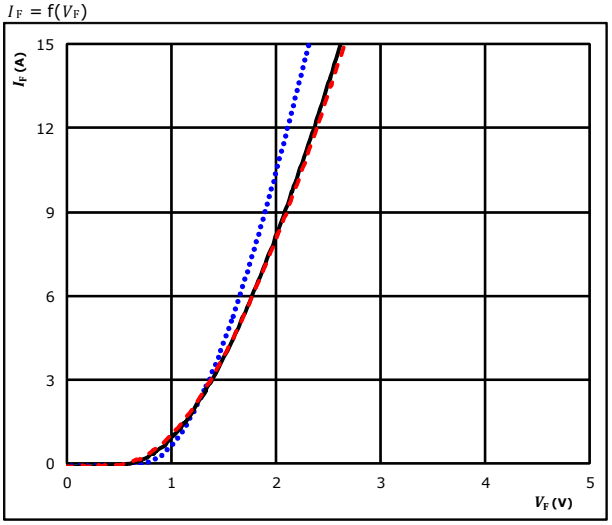
R (K/W)	τ (s)
5,40E-02	3,36E+00
1,45E-01	4,86E-01
5,42E-01	9,83E-02
3,02E-01	2,38E-02
1,17E-01	4,48E-03
7,51E-02	3,80E-04

Brake Sw. Protection Diode Characteristics

figure 1. **FWD**

Typical forward characteristics

$I_F = f(V_F)$



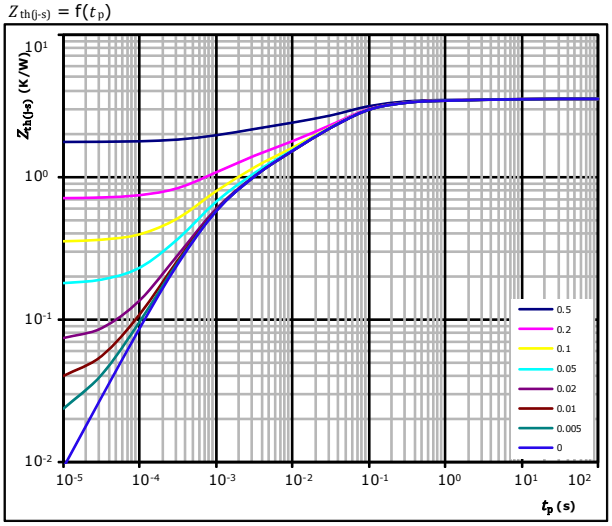
t_p = 250 µs

T_j: 25 °C, 125 °C, 150 °C

figure 2. **FWD**

Transient thermal impedance as a function of pulse width

$Z_{th(j-s)} = f(t_p)$



$D = t_p / T$

$R_{th(j-s)}$ = 3,50 K/W

FWD thermal model values

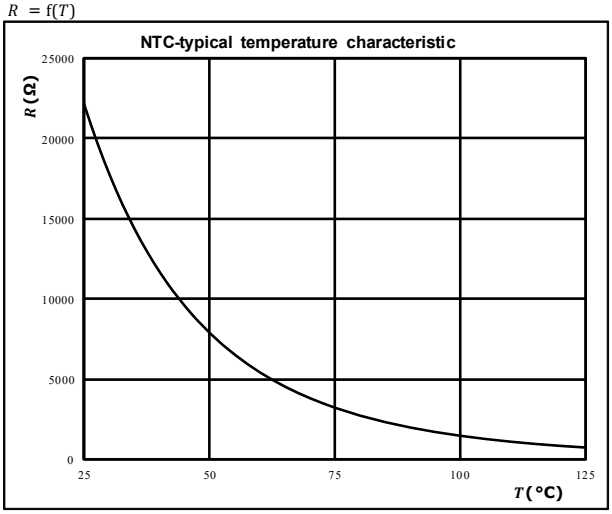
R (K/W)	τ (s)
8,03E-02	7,23E+00
2,34E-01	4,70E-01
1,33E+00	6,36E-02
7,92E-01	2,24E-02
5,71E-01	3,34E-03
4,85E-01	7,05E-04

Thermistor Characteristics

figure 1. **Thermistor**

Typical NTC characteristic
as a function of temperature

$R = f(T)$

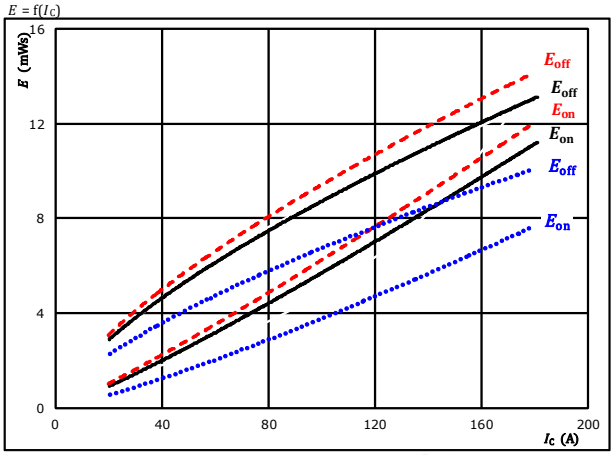


Inverter Switching Characteristics

figure 1. **IGBT**

Typical switching energy losses as a function of collector current

$E = f(I_C)$



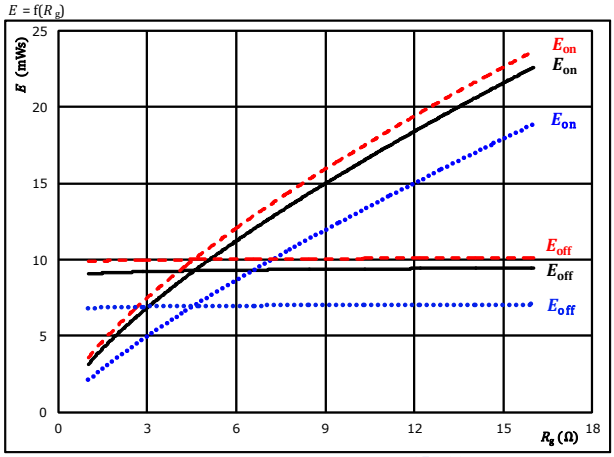
With an inductive load at

V_{CE} =	600	V	T_j:	25 °C	
V_{GE} =	±15	V		125 °C	
R_{gon} =	2	Ω		150 °C	
R_{goff} =	2	Ω			

figure 2. **IGBT**

Typical switching energy losses as a function of gate resistor

$E = f(R_g)$



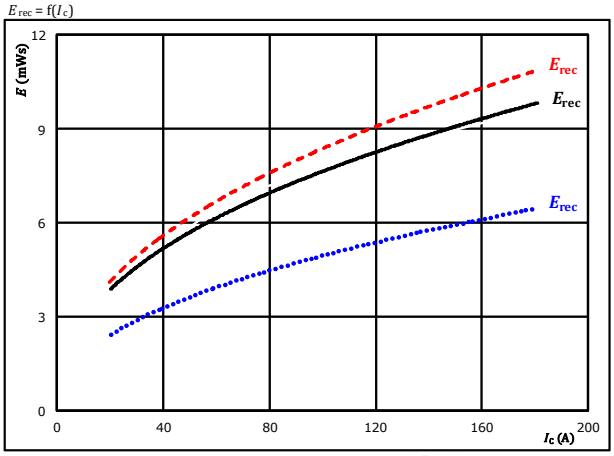
With an inductive load at

V_{CE} =	600	V	T_j:	25 °C	
V_{GE} =	±15	V		125 °C	
I_C =	100	A		150 °C	

figure 3. **FWD**

Typical reverse recovered energy loss as a function of collector current

$E_{rec} = f(I_C)$



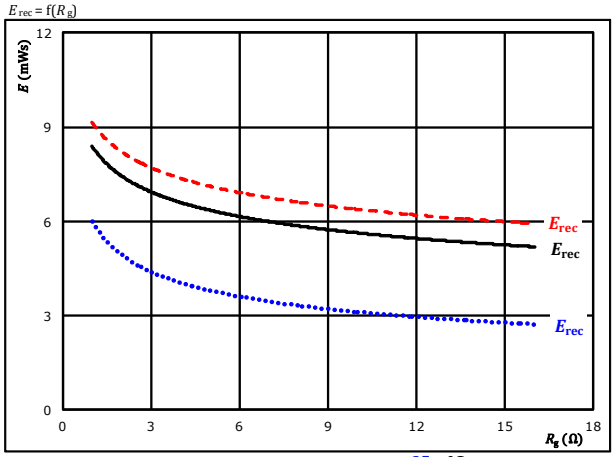
With an inductive load at

V_{CE} =	600	V	T_j:	25 °C	
V_{GE} =	±15	V		125 °C	
R_{gon} =	2	Ω		150 °C	

figure 4. **FWD**

Typical reverse recovered energy loss as a function of gate resistor

$E_{rec} = f(R_g)$



With an inductive load at

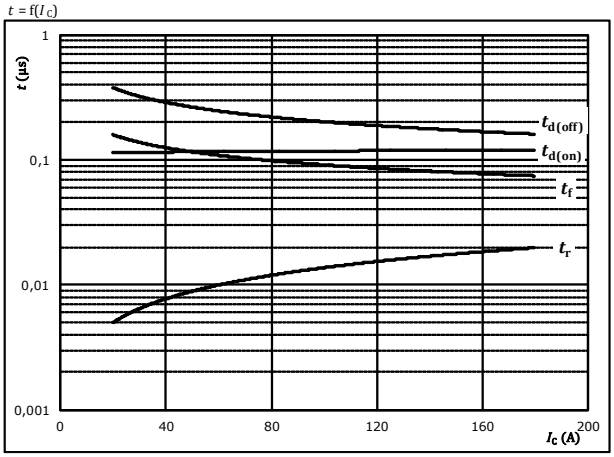
V_{CE} =	600	V	T_j:	25 °C	
V_{GE} =	±15	V		125 °C	
I_C =	100	A		150 °C	

Inverter Switching Characteristics

figure 5. **IGBT**

Typical switching times as a function of collector current

$t = f(I_C)$



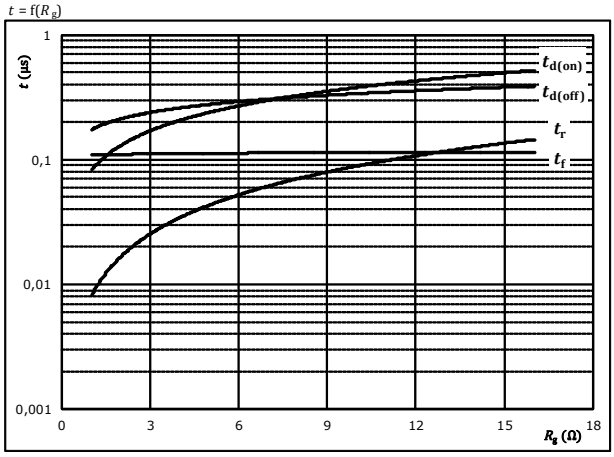
With an inductive load at

T_j =	150	°C
V_{CE} =	600	V
V_{GE} =	±15	V
R_{gon} =	2	Ω
R_{goff} =	2	Ω

figure 6. **IGBT**

Typical switching times as a function of gate resistor

$t = f(R_g)$



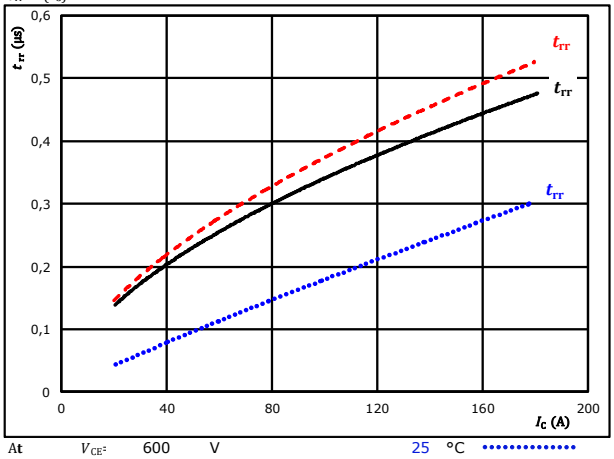
With an inductive load at

T_j =	150	°C
V_{CE} =	600	V
V_{GE} =	±15	V
I_C =	100	A

figure 7. **FWD**

Typical reverse recovery time as a function of collector current

$t_{rr} = f(I_C)$

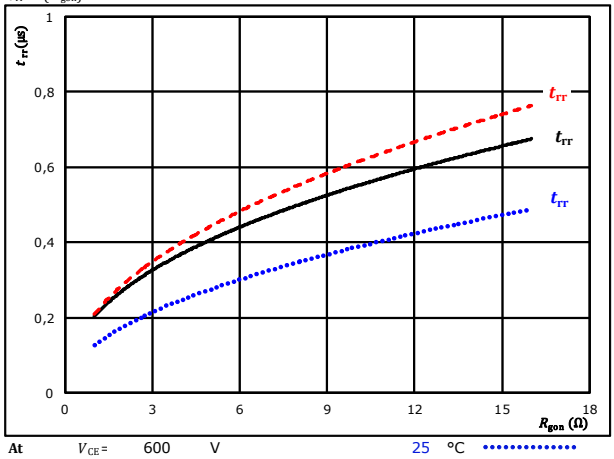


At	V_{CE} =	600	V		25 °C
	V_{GE} =	±15	V	T_j:	125 °C
	R_{gon} =	2	Ω		150 °C

figure 8. **FWD**

Typical reverse recovery time as a function of IGBT turn on gate resistor

$t_{rr} = f(R_{gon})$



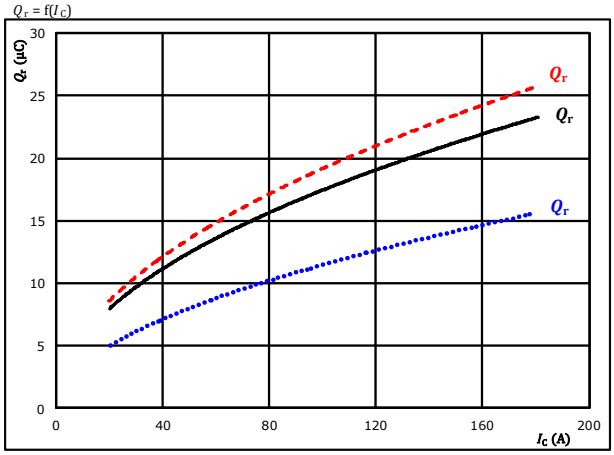
At	V_{CE} =	600	V		25 °C
	V_{GE} =	±15	V	T_j:	125 °C
	I_C =	100	A		150 °C

Inverter Switching Characteristics

figure 9. FWD

Typical recovered charge as a function of collector current

$Q_r = f(I_C)$

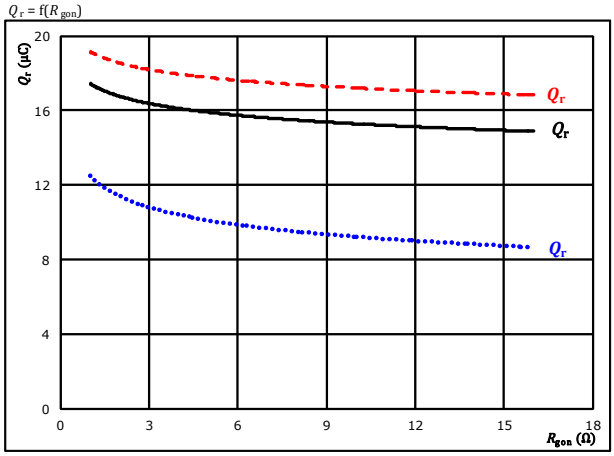


At						
	V_{CE} =	600	V		25 °C	
	V_{GE} =	±15	V	T_j:	125 °C	
	R_{gon} =	2	Ω		150 °C	

figure 10. FWD

Typical recovered charge as a function of IGBT turn on gate resistor

$Q_r = f(R_{gon})$

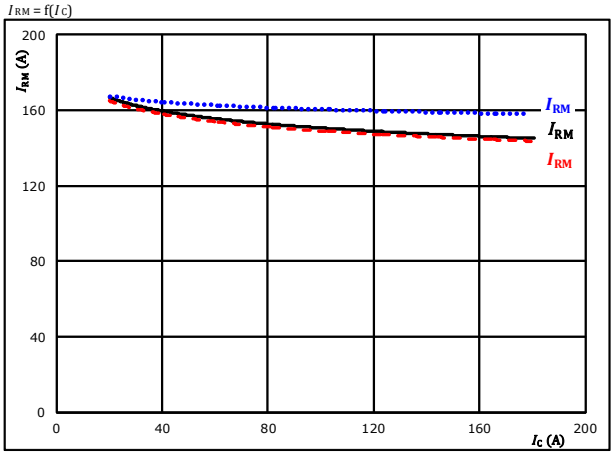


At						
	V_{CE}=	600	V		25 °C	
	V_{GE} =	±15	V	T_j:	125 °C	
	I_C=	100	A		150 °C	

figure 11. FWD

Typical peak reverse recovery current current as a function of collector current

$I_{RM} = f(I_C)$

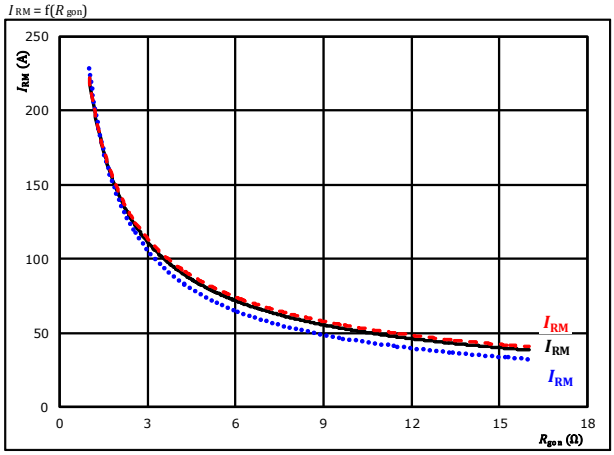


At						
	V_{CE}:	600	V		25 °C	
	V_{GE} =	±15	V	T_j:	125 °C	
	R_{gon} =	2	Ω		150 °C	

figure 12. FWD

Typical peak reverse recovery current as a function of IGBT turn on gate resistor

$I_{RM} = f(R_{gon})$



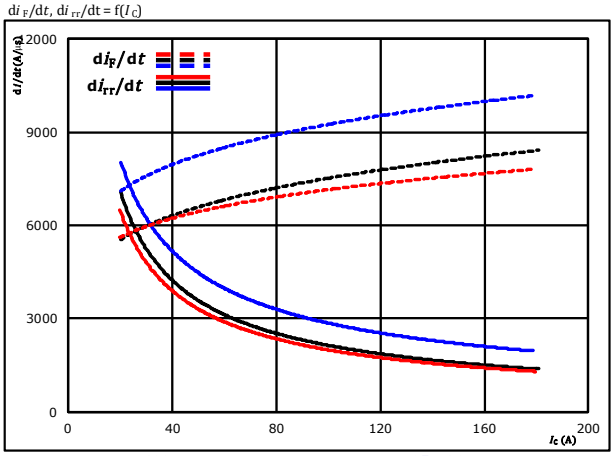
At						
	V_{CE} =	600	V		25 °C	
	V_{GE} =	±15	V	T_j:	125 °C	
	I_C =	100	A		150 °C	

Inverter Switching Characteristics

figure 13. **FWD**

Typical rate of fall of forward and reverse recovery current as a function of collector current

$di_F/dt, di_{rr}/dt = f(I_C)$

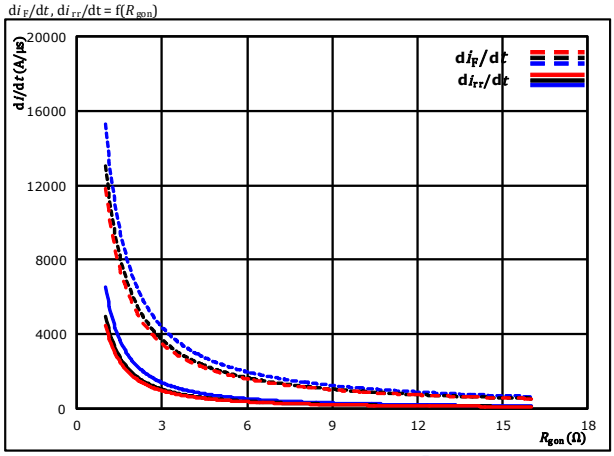


At						
V_{CE}:	600	V		25	°C	•••••••••••••••
V_{GE} =	±15	V	T_j:	125	°C	———
R_{gon} =	2	Ω		150	°C	- - - -

figure 14. **FWD**

Typical rate of fall of forward and reverse recovery current as a function of IGBT turn on gate resistor

$di_F/dt, di_{rr}/dt = f(R_{gon})$

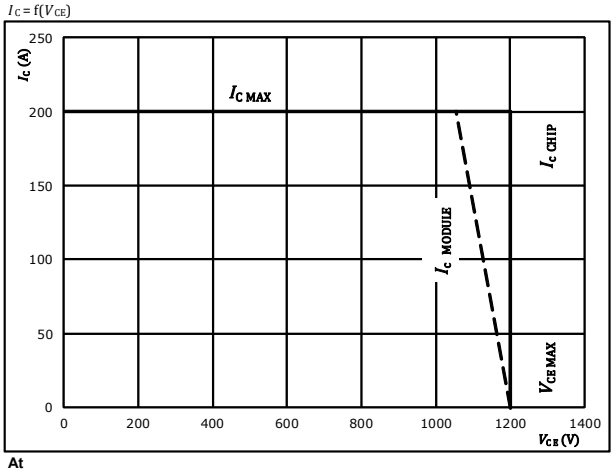


At						
V_{CE} =	600	V		25	°C	•••••••••••••••
V_{GE} =	±15	V	T_j:	125	°C	———
I_C =	100	A		150	°C	- - - -

figure 15. **IGBT**

Reverse bias safe operating area

$I_C = f(V_{CE})$



At

T_j =	175	°C
R_{gon} =	2	Ω
R_{goff} =	2	Ω

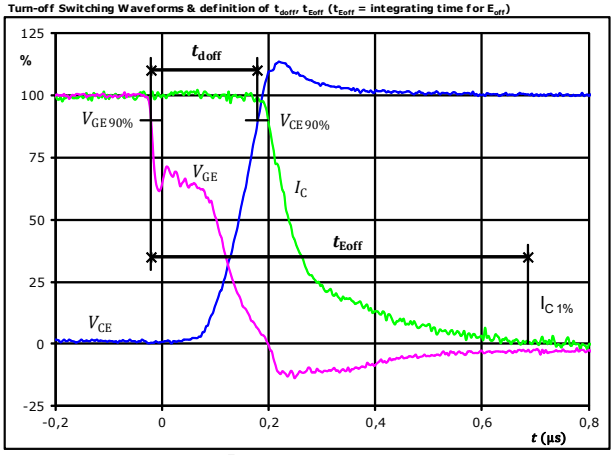
Inverter Switching Definitions

General conditions

T_j	=	125 °C
R_{gon}	=	2 Ω
R_{goff}	=	2 Ω

figure 1. IGBT

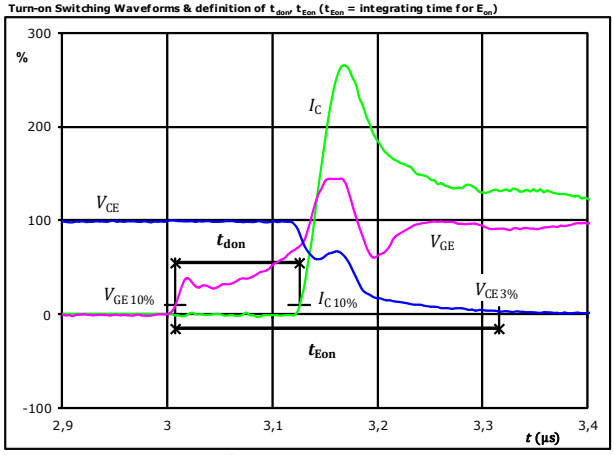
Turn-off Switching Waveforms & definition of t_{doff}, t_{Eoff} (t_{Eoff} = integrating time for E_{off})



$V_{GE}(0\%)$ =	-15	V
$V_{GE}(100\%)$ =	15	V
$V_C(100\%)$ =	600	V
$I_C(100\%)$ =	100	A
t_{doff} =	0,200	µs
t_{Eoff} =	0,707	µs

figure 2. IGBT

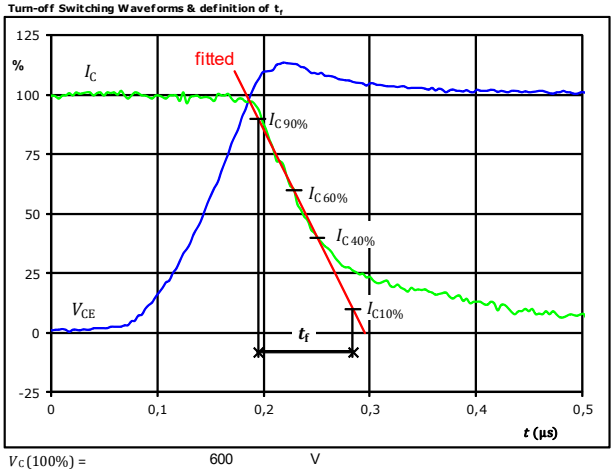
Turn-on Switching Waveforms & definition of t_{don}, t_{Eon} (t_{Eon} = integrating time for E_{on})



$V_{GE}(0\%)$ =	-15	V
$V_{GE}(100\%)$ =	15	V
$V_C(100\%)$ =	600	V
$I_C(100\%)$ =	100	A
t_{don} =	0,118	µs
t_{Eon} =	0,308	µs

figure 3. IGBT

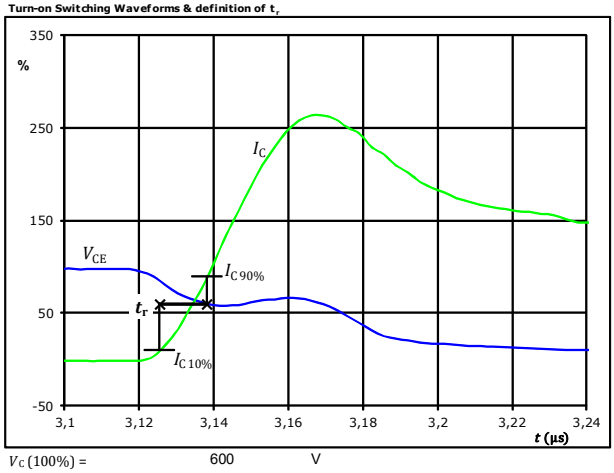
Turn-off Switching Waveforms & definition of t_f



$V_C(100\%)$ =	600	V
$I_C(100\%)$ =	100	A
t_f =	0,096	µs

figure 4. IGBT

Turn-on Switching Waveforms & definition of t_r

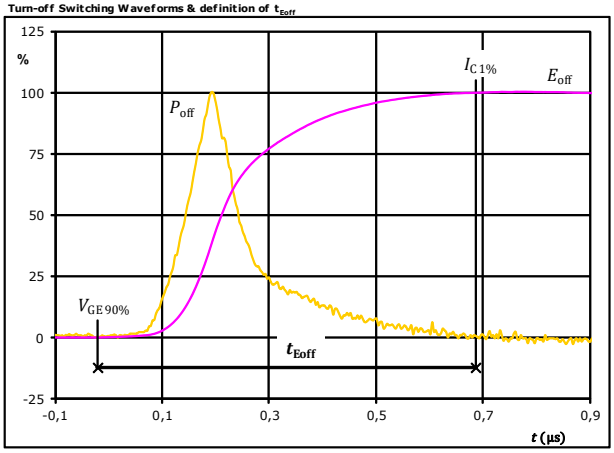


$V_C(100\%)$ =	600	V
$I_C(100\%)$ =	100	A
t_r =	0,012	µs

Inverter Switching Characteristics

figure 5. **IGBT**

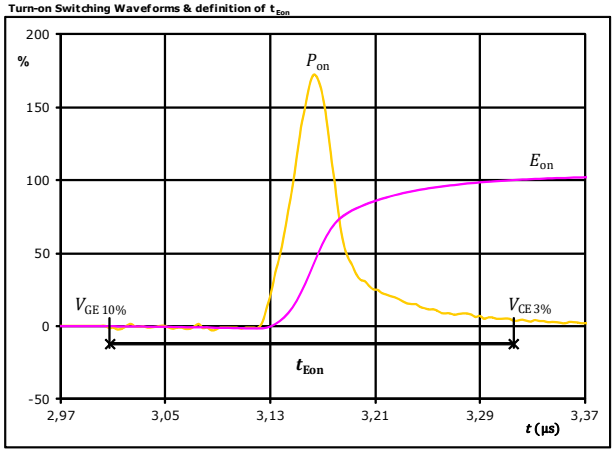
Turn-off Switching Waveforms & definition of t_{Eoff}



$P_{off}(100\%)$ =	59,87	kW
$E_{off}(100\%)$ =	8,77	mJ
t_{Eoff} =	0,71	µs

figure 6. **IGBT**

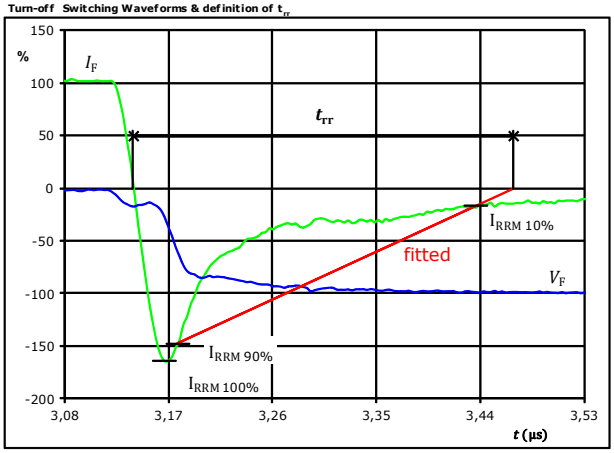
Turn-on Switching Waveforms & definition of t_{Eon}



$P_{on}(100\%)$ =	59,87	kW
$E_{on}(100\%)$ =	4,87	mJ
t_{Eon} =	0,31	µs

figure 7. **FWD**

Turn-off Switching Waveforms & definition of t_{rr}

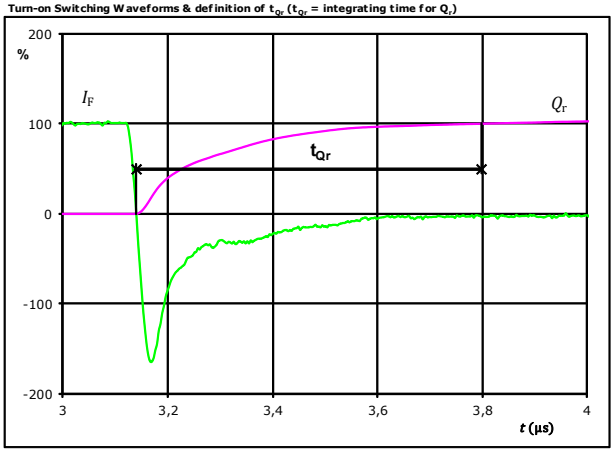


$V_F(100\%)$ =	600	V
$I_F(100\%)$ =	100	A
$I_{RRM}(100\%)$ =	-166	A
t_{rr} =	0,312	µs

Inverter Switching Characteristics

figure 8. **FWD**

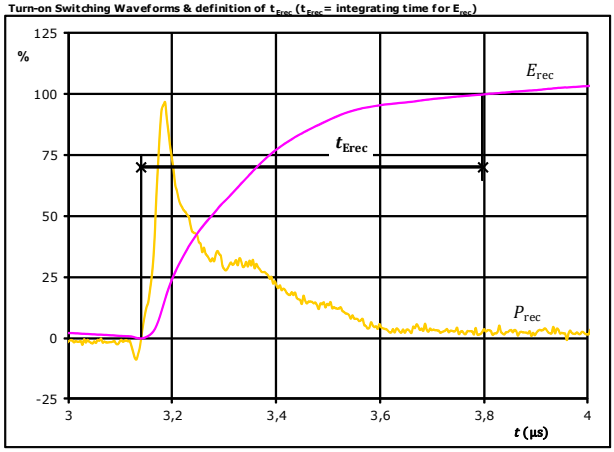
Turn-on Switching Waveforms & definition of t_{Qr} (t_{Qr} = integrating time for Q_r)



I_F (100%) =	100	A
Q_r (100%) =	17,27	µC
t_{Qr} =	0,66	µs

figure 9. **FWD**

Turn-on Switching Waveforms & definition of t_{Erec} (t_{Erec} = integrating time for E_{rec})



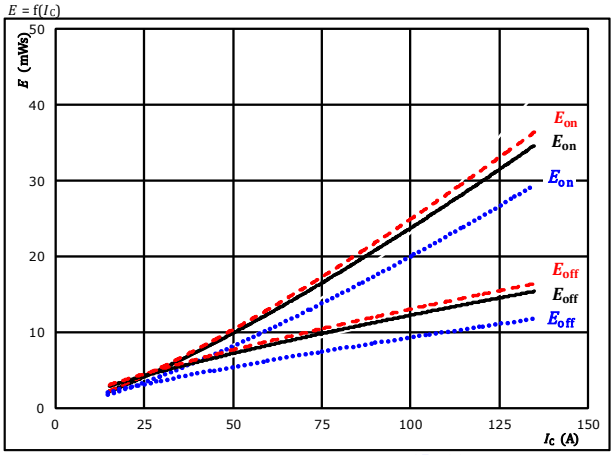
P_{rec} (100%) =	59,87	kW
E_{rec} (100%) =	7,75	mJ
t_{Erec} =	0,66	µs

Brake Switching Characteristics

figure 1. IGBT

Typical switching energy losses as a function of collector current

$E = f(I_C)$



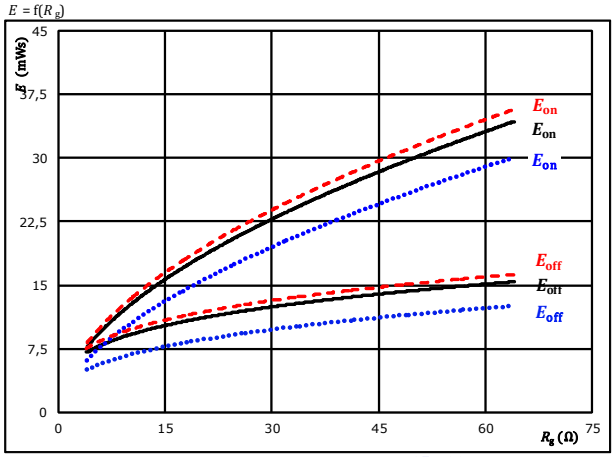
With an inductive load at

V_{CE} =	700	V	T_j:	25 °C
V_{GE} =	15/0	V		125 °C
R_{gon} =	16	Ω		150 °C
R_{goff} =	16	Ω		

figure 2. IGBT

Typical switching energy losses as a function of gate resistor

$E = f(R_g)$



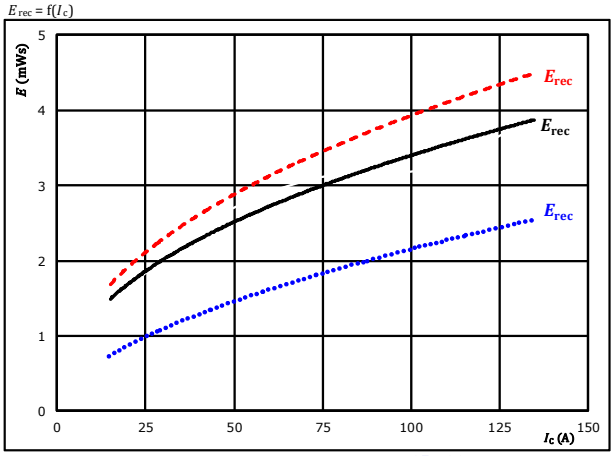
With an inductive load at

V_{CE} =	700	V	T_j:	25 °C
V_{GE} =	15/0	V		125 °C
I_C =	75	A		150 °C

figure 3. FWD

Typical reverse recovered energy loss as a function of collector current

$E_{rec} = f(I_c)$



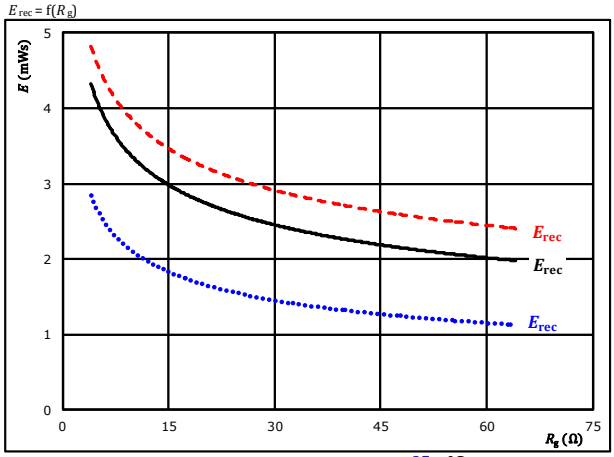
With an inductive load at

V_{CE} =	700	V	T_j:	25 °C
V_{GE} =	15/0	V		125 °C
R_{gon} =	16	Ω		150 °C

figure 4. FWD

Typical reverse recovered energy loss as a function of gate resistor

$E_{rec} = f(R_g)$



With an inductive load at

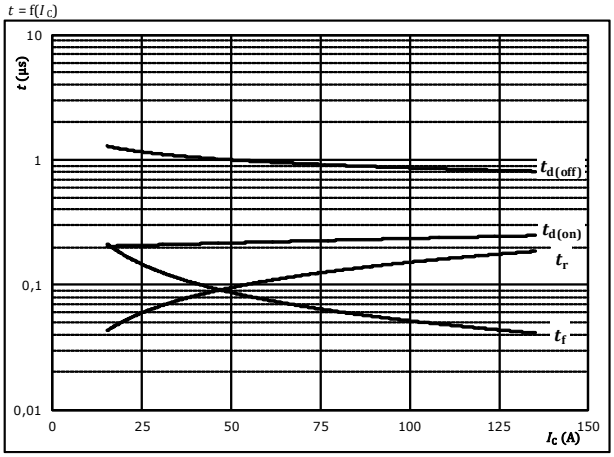
V_{CE} =	700	V	T_j:	25 °C
V_{GE} =	15/0	V		125 °C
I_C =	75	A		150 °C

Brake Switching Characteristics

figure 5. IGBT

Typical switching times as a function of collector current

$t = f(I_C)$



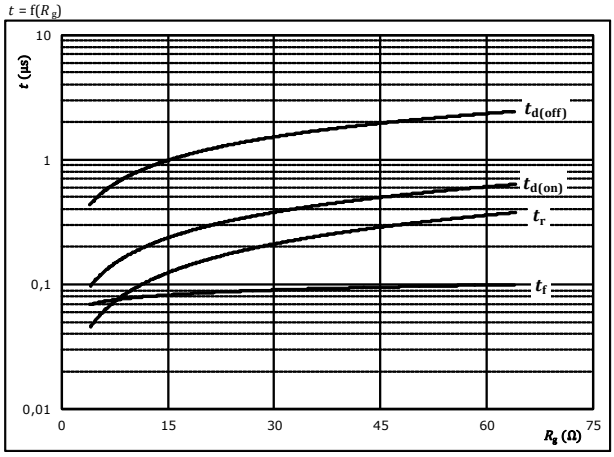
With an inductive load at

T_j =	150	°C
V_{CE} =	700	V
V_{GE} =	15/0	V
R_{gon} =	16	Ω
R_{goff} =	16	Ω

figure 6. IGBT

Typical switching times as a function of gate resistor

$t = f(R_g)$



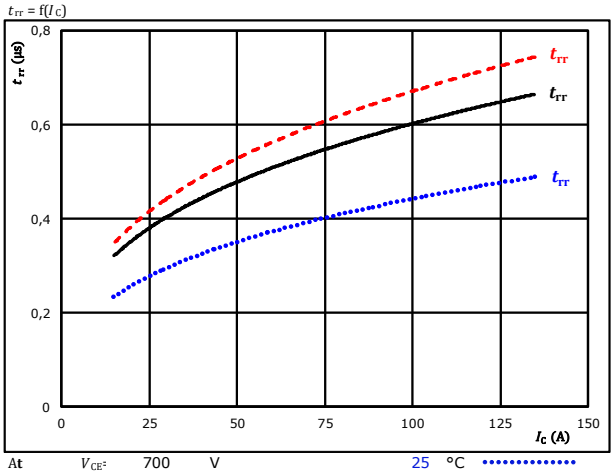
With an inductive load at

T_j =	150	°C
V_{CE} =	700	V
V_{GE} =	15/0	V
I_C =	75	A

figure 7. FWD

Typical reverse recovery time as a function of collector current

$t_{rr} = f(I_C)$



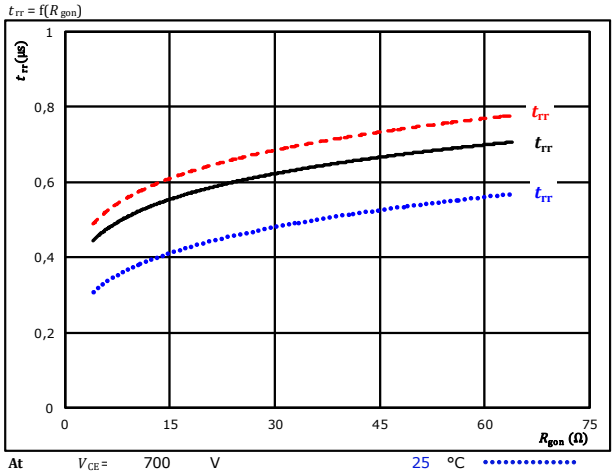
At

V_{CE} =	700	V	T_j:	25	°C
V_{GE} =	15/0	V		125	°C
R_{gon} =	16	Ω		150	°C

figure 8. FWD

Typical reverse recovery time as a function of IGBT turn on gate resistor

$t_{rr} = f(R_{gon})$



At

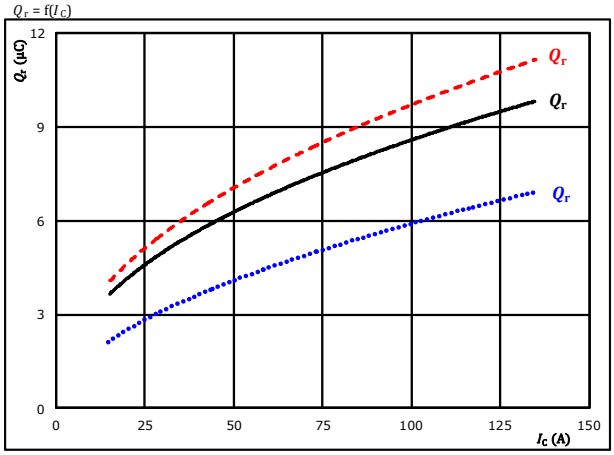
V_{CE} =	700	V	T_j:	25	°C
V_{GE} =	15/0	V		125	°C
I_C =	75	A		150	°C

Brake Switching Characteristics

figure 9. FWD

Typical recovered charge as a function of collector current

$Q_r = f(I_C)$

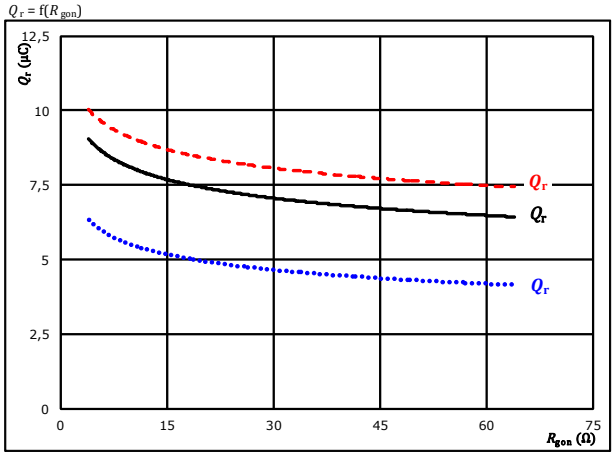


At						
	V_{CE} =	700	V		25 °C	
	V_{GE} =	15/0	V	T_j:	125 °C	
	R_{gon} =	16	Ω		150 °C	

figure 10. FWD

Typical recovered charge as a function of IGBT turn on gate resistor

$Q_r = f(R_{gon})$

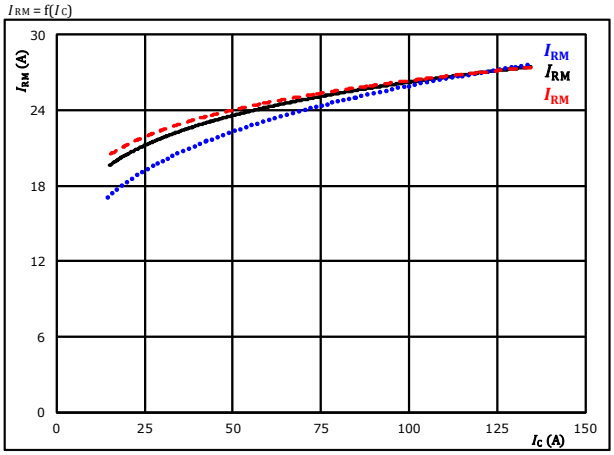


At						
	V_{CE}=	700	V		25 °C	
	V_{GE} =	15/0	V	T_j:	125 °C	
	I_C=	75	A		150 °C	

figure 11. FWD

Typical peak reverse recovery current current as a function of collector current

$I_{RM} = f(I_C)$

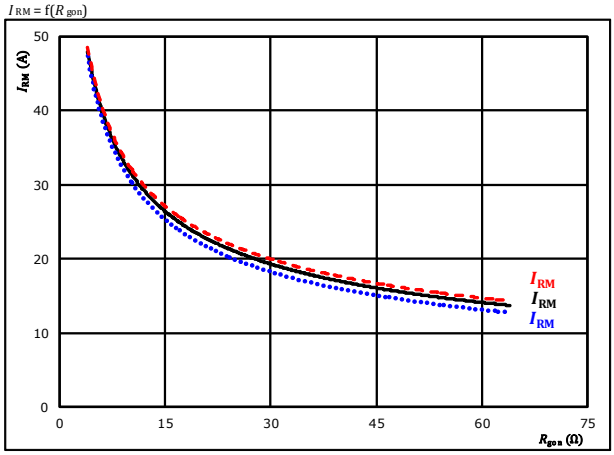


At						
	V_{CE}:	700	V		25 °C	
	V_{GE} =	15/0	V	T_j:	125 °C	
	R_{gon} =	16	Ω		150 °C	

figure 12. FWD

Typical peak reverse recovered current as a function of IGBT turn on gate resistor

$I_{RM} = f(R_{gon})$



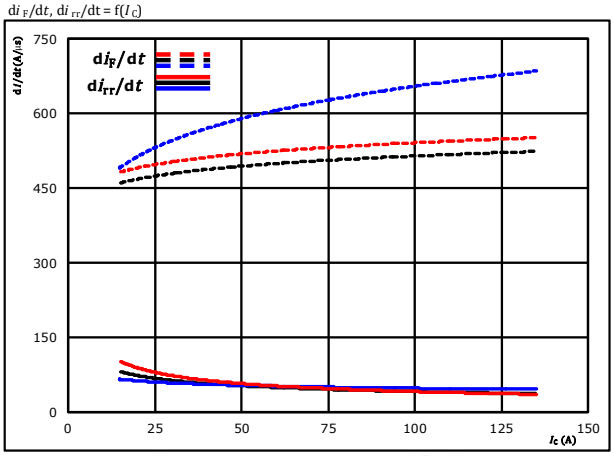
At						
	V_{CE} =	700	V		25 °C	
	V_{GE} =	15/0	V	T_j:	125 °C	
	I_C =	75	A		150 °C	

Brake Switching Characteristics

figure 13. **FWD**

Typical rate of fall of forward and reverse recovery current as a function of collector current

$di_F/dt, di_{rr}/dt = f(I_C)$

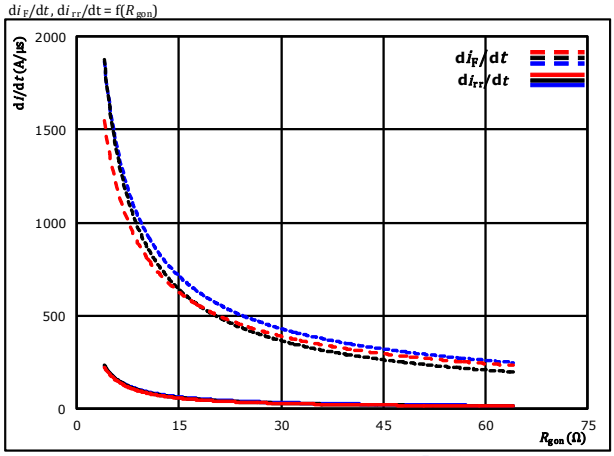


At						
V_{CE}:	700	V		25	°C	•••••••••••••
V_{GE} =	15/0	V	T_j:	125	°C	———
R_{gon} =	16	Ω		150	°C	- - - -

figure 14. **FWD**

Typical rate of fall of forward and reverse recovery current as a function of IGBT turn on gate resistor

$di_F/dt, di_{rr}/dt = f(R_{gon})$

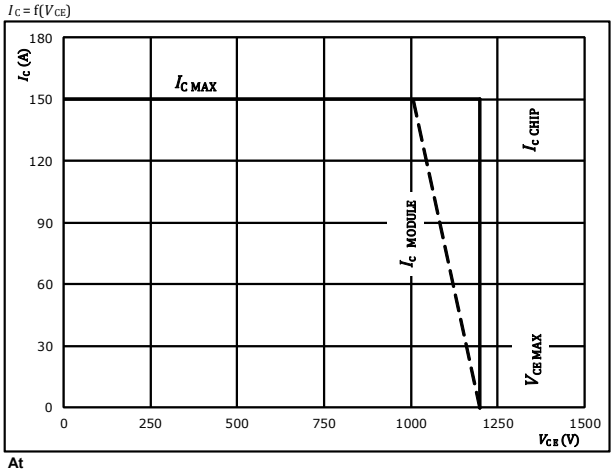


At						
V_{CE} =	700	V		25	°C	•••••••••••••
V_{GE} =	15/0	V	T_j:	125	°C	———
I_C =	75	A		150	°C	- - - -

figure 15. **IGBT**

Reverse bias safe operating area

$I_C = f(V_{CE})$



At

T_j =	175	°C
R_{gon} =	16	Ω
R_{goff} =	16	Ω

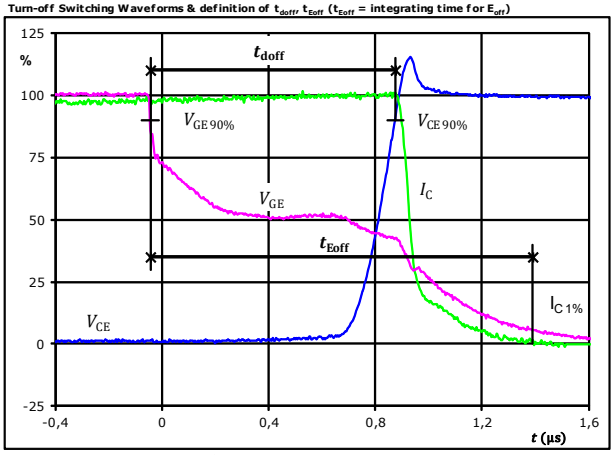
Brake Switching Definitions

General conditions

T_j	=	125 °C
R_{gon}	=	16 Ω
R_{goff}	=	16 Ω

figure 1. IGBT

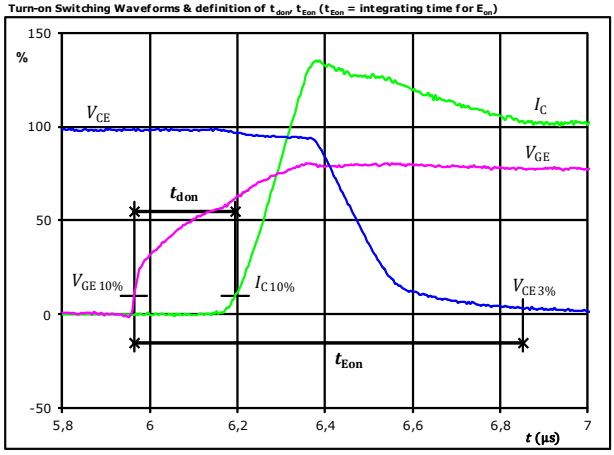
Turn-off Switching Waveforms & definition of t_{doff}, t_{Eoff} (t_{Eoff} = integrating time for E_{off})



$V_{GE}(0\%)$ =	0	V
$V_{GE}(100\%)$ =	15	V
$V_C(100\%)$ =	700	V
$I_C(100\%)$ =	75	A
t_{doff} =	0,919	µs
t_{Eoff} =	1,434	µs

figure 2. IGBT

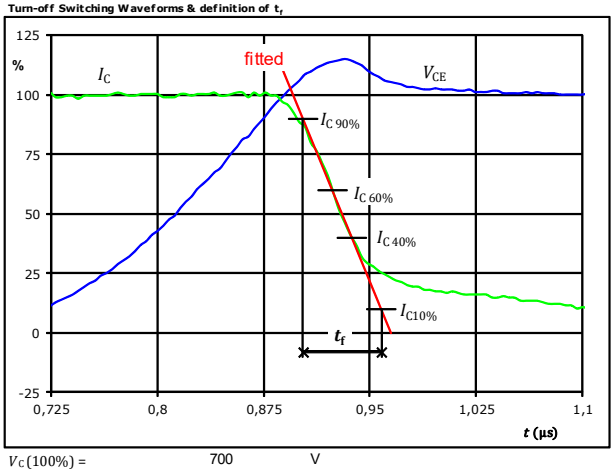
Turn-on Switching Waveforms & definition of t_{don}, t_{Eon} (t_{Eon} = integrating time for E_{on})



$V_{GE}(0\%)$ =	0	V
$V_{GE}(100\%)$ =	15	V
$V_C(100\%)$ =	700	V
$I_C(100\%)$ =	75	A
t_{don} =	0,232	µs
t_{Eon} =	0,888	µs

figure 3. IGBT

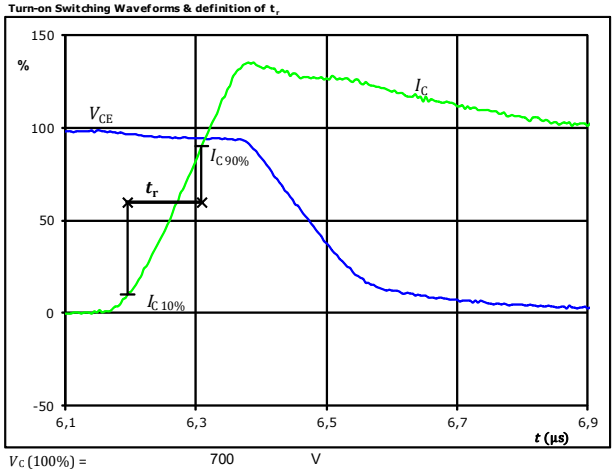
Turn-off Switching Waveforms & definition of t_f



$V_C(100\%)$ =	700	V
$I_C(100\%)$ =	75	A
t_f =	0,054	µs

figure 4. IGBT

Turn-on Switching Waveforms & definition of t_r

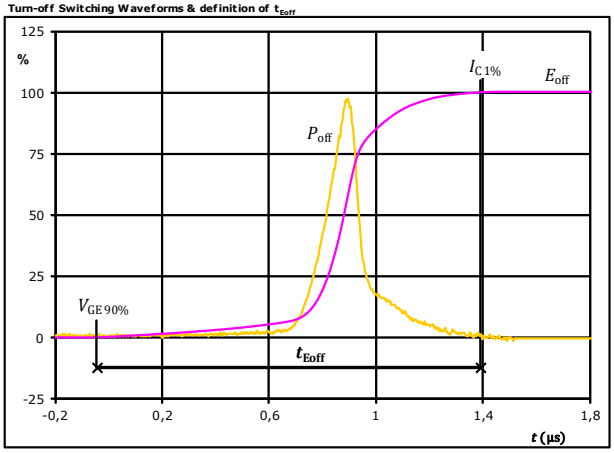


$V_C(100\%)$ =	700	V
$I_C(100\%)$ =	75	A
t_r =	0,113	µs

Brake Switching Characteristics

figure 5. **IGBT**

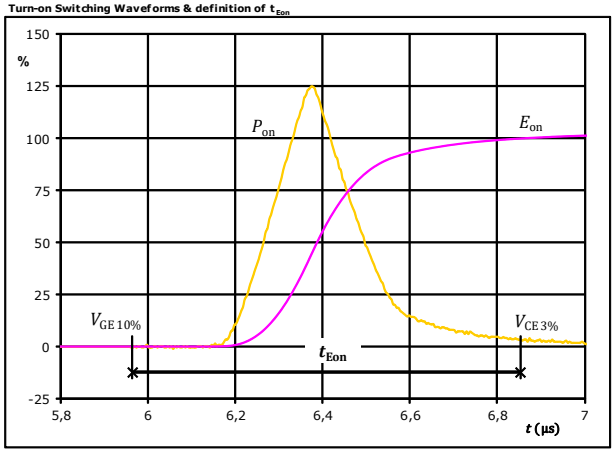
Turn-off Switching Waveforms & definition of t_{Eoff}



$P_{off}\,(100\%)$ =	52,35	kW
$E_{off}\,(100\%)$ =	9,35	mJ
t_{Eoff} =	1,43	µs

figure 6. **IGBT**

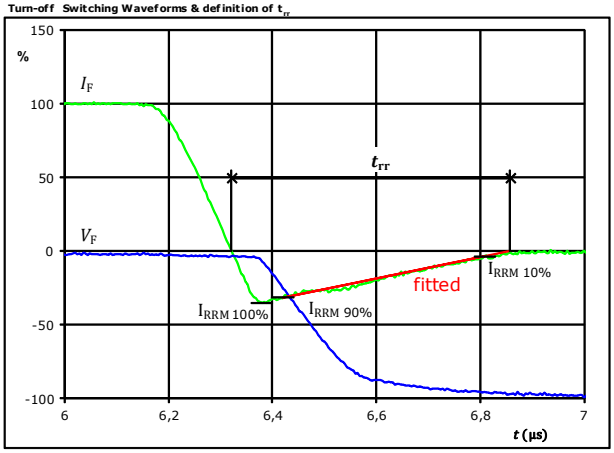
Turn-on Switching Waveforms & definition of t_{Eon}



$P_{on}\,(100\%)$ =	52,35	kW
$E_{on}\,(100\%)$ =	14,53	mJ
t_{Eon} =	0,89	µs

figure 7. **FWD**

Turn-off Switching Waveforms & definition of t_{rr}

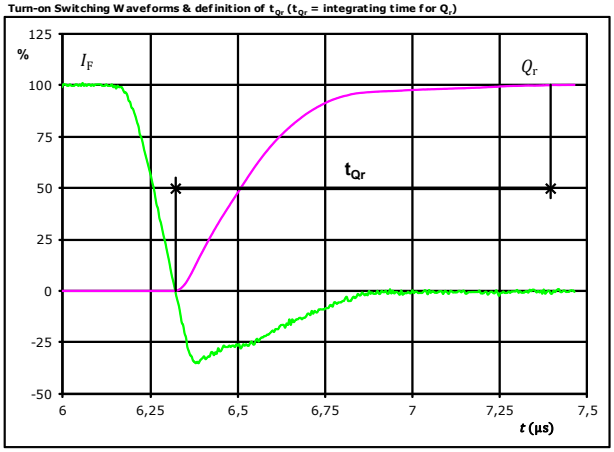


$V_F\,(100\%)$ =	700	V
$I_F\,(100\%)$ =	75	A
$I_{RRM}\,(100\%)$ =	-26	A
t_{rr} =	0,540	µs

Brake Switching Characteristics

figure 8. **FWD**

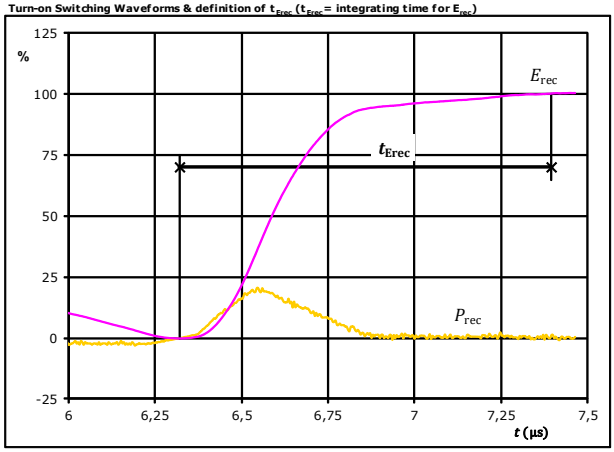
Turn-on Switching Waveforms & definition of t_{Qr} (t_{Qr} = integrating time for Q_r)



I_F (100%) =	75	A
Q_r (100%) =	7,70	µC
t_{Qr} =	1,07	µs

figure 9. **FWD**

Turn-on Switching Waveforms & definition of t_{Erec} (t_{Erec} = integrating time for E_{rec})



P_{rec} (100%) =	52,35	kW
E_{rec} (100%) =	3,11	mJ
t_{Erec} =	1,07	µs

Vincotech

30-F212PMA100M7-L880A79
30-P212PMA100M7-L880A79Y
datasheet

Ordering Code & Marking

Version	Ordering Code
without thermal paste 17 mm housing with solder pins	30-F212PMA100M7-L880A79
without thermal paste 17 mm housing with solder pins	30-F212PMA100M7-L880A79-/3/
with thermal paste 17 mm housing with solder pins	30-P212PMA100M7-L880A79Y
without thermal paste 17 mm housing with press-fit pins	30-P212PMA100M7-L880A79Y-/3/

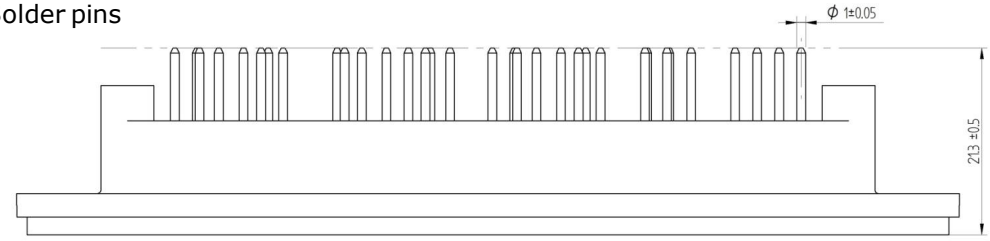
	Name		Date code	UL & VIN	Lot	Serial
Text	NN-NNNNNNNNNNNNN-TTTTTTVV		WWYY	UL VIN	LLLLL	SSSS
	Type&Ver	**Lot number**	**Serial**	**Date code**		
Datamatrix	TTTTTTVV	LLLLL	SSSS	WWYY		

Outline

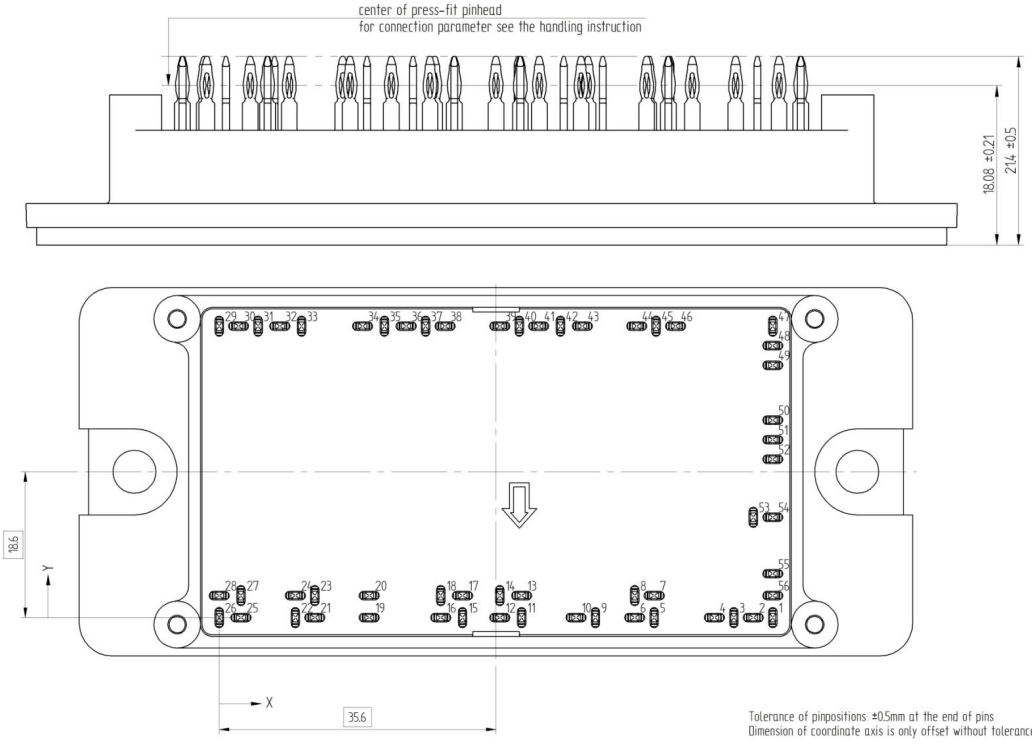
Pin table

Pin	X	Y	Function	Pin	X	Y	Function
1	71,2	0	DC-Rect	52	71,2	20,2	ACIn3
2	68,7	0	DC-Rect	53	71,2	12,8	Br
3	66,2	0	DC-Rect	54	68,7	12,8	Br
4	63,7	0	DC-Rect	55	71,2	5,6	G27
5	55,95	0	DC+Rect	56	71,2	2,8	DC-Br
6	53,45	0	DC+Rect	52	71,2	20,2	ACIn3
7	55,95	2,8	DC+Rect	53	71,2	12,8	Br
8	53,45	2,8	DC+Rect	54	68,7	12,8	Br
9	48,4	0	DC+Inv1	55	71,2	5,6	G27
10	45,9	0	DC+Inv1	56	71,2	2,8	DC-Br
11	38,9	0	S11				
12	36,1	0	DC-1				
13	38,9	2,8	G11				
14	36,1	2,8	DC-1				
15	31,3	0	DC-2				
16	28,5	0	S13				
17	31,3	2,8	DC-2				
18	28,5	2,8	G13				
19	19,3	0	Therm2				
20	19,3	2,8	Therm1				
21	12,3	0	DC+Inv2				
22	9,8	0	DC+Inv2				
23	12,3	2,8	DC+Inv2				
24	9,8	2,8	DC+Inv2				
25	2,8	0	S15				
26	0	0	DC-3				
27	2,8	2,8	G15				
28	0	2,8	DC-3				
29	0	37,2	Ph3				
30	2,5	37,2	Ph3				
31	5	37,2	Ph3				
32	7,8	37,2	S16				
33	10,6	37,2	G16				
34	18,45	37,2	G14				
35	21,25	37,2	S14				
36	24,05	37,2	Ph2				
37	26,55	37,2	Ph2				
38	29,05	37,2	Ph2				
39	36,1	37,2	Ph1				
40	38,6	37,2	Ph1				
41	41,1	37,2	Ph1				
42	43,9	37,2	S12				
43	46,7	37,2	G12				
44	53,7	37,2	ACIn1				
45	56,2	37,2	ACIn1				
46	58,7	37,2	ACIn1				
47	71,2	37,2	ACIn2				
48	71,2	34,7	ACIn2				
49	71,2	32,2	ACIn2				
50	71,2	25,2	ACIn3				
51	71,2	22,7	ACIn3				

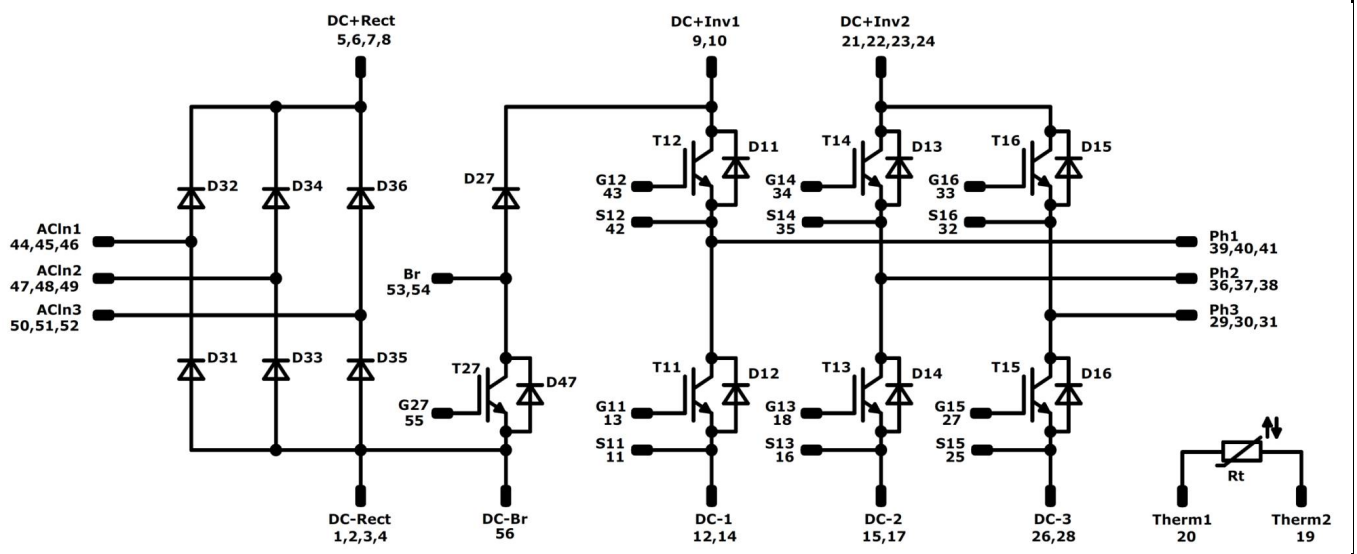
Solder pins



Press-fit pins



Pinout



Identification

ID	Component	Voltage	Current	Function	Comment
D31, D32, D33, D34, D35, D36	Rectifier	1600 V	75 A	Rectifier	
T11, T12, T13, T14, T15, T16	IGBT	1200 V	100 A	Inverter Switch	
D11, D12, D13, D14, D15, D16	FWD	1200 V	100 A	Inverter Diode	
T27	IGBT	1200 V	75 A	Brake Switch	
D27	FWD	1200 V	35 A	Brake Diode	
D47	Diode	1200 V	5 A	Brake Sw. Protection Diode	

Packaging instruction				
Standard packaging quantity (SPQ) 36	>SPQ	Standard	<SPQ	Sample

Handling instruction
Handling instructions for *flow* 2 packages see vincotech.com website.

Package data
Package data for *flow* 2 packages see vincotech.com website.

UL recognition and file number
This device is certified according to UL 1557 standard, UL file number E192116. For more information see vincotech.com website.

Document No.:	Date:	Modification:	Pages
30-x212PMA100M7-L880A79x-D1-14	05 Dec. 2017		